

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1	(chamber same (substrate or carrier or base or plate or wafer)) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate) and (amorphous near carbon) same hydrogen and (process\$4 same gas) and plasma and rf near (power or source) and (etch \$4 or remov\$4 or photolithograph\$8) same carbon and (etch\$4 same remov\$4) same(ARC or (ar near coat\$4) or (anti adj reflective)) and (pattern same resist) and (257/437. ccis.) and hydrocarbon	US-PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:20
S1	107	((("6635583B2") or ("6624064B1") or ("6573030") or ("6541397B1") or ("6458516B1") or ("6423384B1") or ("6413852") or ("6380106") or ("6358573B1") or ("6333255") or ("6331380B1") or ("6323119B1") or ("6316347") or ("6291334B1") or ("6235629") or ("6214730") or ("6211065B1") or ("6165890") or ("6153935") or ("6143476") or ("6140226") or ("6140224") or ("6098568") or ("6080529") or ("6066577") or ("6064118") or ("6057226") or ("6035803") or ("6030901") or ("6008140") or	US-PGPUB; USPAT; USOOR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/30 08:12

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((2003/0091938A1) or
(2002/0090794A1) or
(2002/0086547A1) or
(2002/0001778A1) or
(2001/0007788A1) or
(2004/0038537A1) or
(2004/0023502) or
(2004/0166691A1) or
(2004/0180551A1) or
(2004/0038537) or
(2004/0229470)).COLS.

S2	7	Si and (substrate or wafer or semiconductor) and chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetylene) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 (carbon))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/14 08:22
S3	6	Si and (substrate or wafer or semiconductor) and chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetylene) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 (carbon)) and (hydrogen or oxygen)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/14 08:23
S4	1	Si and (substrate or wafer or semiconductor) and chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetylene) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 (carbon)) and (hydrogen or oxygen) and etch\$4 and resist and ("silicon nitride" or "silicon carbide" or "carbon-doped silicon oxide" or "amorphous (carbon)") and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/14 08:37
S5	6	(substrate or wafer or semiconductor) and chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetylene) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 (carbon)) and (hydrogen or oxygen) and etch\$4 and resist and ("silicon nitride" or "silicon carbide" or "carbon-doped silicon oxide" or "amorphous (carbon)") and dielectric and "dual frequency"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/16 10:52

S6	2	(substrate or wafer or semiconductor) and (chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetylene) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 carbon) and (hydrogen or oxygen) and etch\$4 and resist and ("silicon nitride" or "silicon carbide" or "carbon-doped silicon oxide" or "amorphous carbon") and dielectric and "dual frequency" and ("ARC" or "anti reflective coating")	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/16 08:41
S7	1	10/799146	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/16 10:52
S8	5	((substrate or semiconductor or wafer) near8 chamber) and (hydrocarbon near8 gas) and argon and plasma and (dual near4 frequency) and (amorphous near4 carbon) and hydrogen and (dielectric or oxide or insulat \$4) and etch\$3 and silicon and oxygen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/30 08:25
S9	4	((substrate or semiconductor or wafer) near8 chamber) and (hydrocarbon near8 gas) and argon and plasma and (dual near4 frequency) and (amorphous near4 carbon) and hydrogen and (dielectric or oxide or insulat \$4) and etch\$3 and silicon and oxygen and (conduct \$4 or metal or polysilicon) and pattern	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/30 08:26

S10	25	(chamber same (substrate or carrier or base or plate or wafer) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate) and (amorphous near carbon) same hydrogen and (process\$4 same gas) and plasma and rf near (power or source) and (etch \$4 or remov\$4 or photolithograph\$8) same carbon and (etch\$4 same remov\$4) same(ARC or (ar near coat\$4) or (anti adj reflective)) and (pattern same resist)	US-PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/27 20:51
S11	1	(chamber same (substrate or carrier or base or plate or wafer) and (dielectric or oxide or insulat\$4) same (substrate or wafer or carrier or base or plate) and (amorphous near carbon) same hydrogen and (process\$4 same gas) and plasma and rf near (power or source) and (etch \$4 or remov\$4 or photolithograph\$8) same carbon and (etch\$4 same remov\$4) same(ARC or (ar near coat\$4) or (anti adj reflective)) and (pattern same resist) and (257/437. col.)	US-PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/27 21:20

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